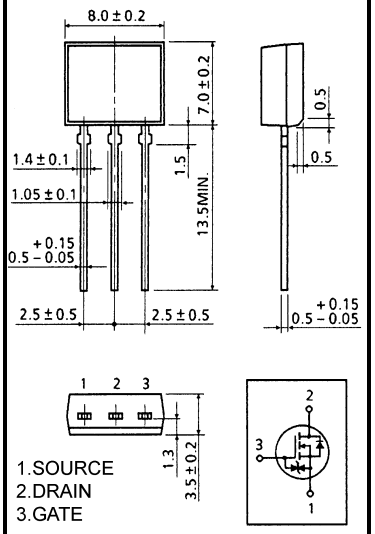
TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L^2−π−MOSV)

2SK2229

Chopper Regulator, DC−DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain−source ON resistance : $R_{DS\ (ON)}$ = 0.12 Ω (typ.)
- High forward transfer admittance : $|Y_{fs}|$ = 5.0 S (typ.)
- Low leakage current : I_{DSS} = 100 μA (max) (V_{DS} = 60 V)
- Enhancement mode : V_{th} = 0.8~2.0 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-8M1B

Weight: 0.54 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain−source voltage		V_{DSS}	60	V
Drain−gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	60	V
Gate−source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	5	A
	Pulse (Note 1)	I_{DP}	20	A
Drain power dissipation		P_D	1.3	W
Single pulse avalanche energy (Note 2)		E_{AS}	129	mJ
Avalanche current		I_{AR}	5	A
Repetitive avalanche energy (Note 3)		E_{AR}	0.13	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

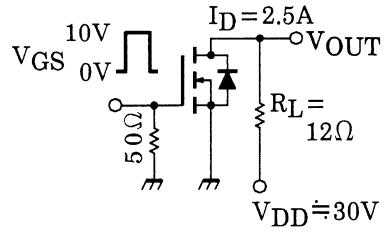
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	$R_{th\ (ch-a)}$	96.1	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.
Note 2: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 7 mH, R_G = 25 Ω, I_{AR} = 5 A
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.
Please handle with caution.

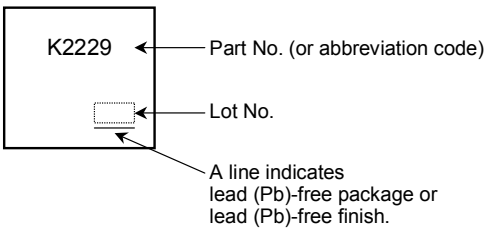
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut−off current		I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V	—	—	100	μA
Drain−source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	60	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	0.8	—	2.0	V
Drain−source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 4 V, I_D = 1.3 A	—	0.20	0.30	Ω
			V_{GS} = 10 V, I_D = 2.5 A	—	0.12	0.16	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 2.5 A	3.0	5.0	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	370	—	pF
Reverse transfer capacitance		C_{rss}		—	60	—	
Output capacitance		C_{oss}		—	180	—	
Switching time	Rise time	t_r		—	18	—	ns
	Turn−on time	t_{on}		—	25	—	
	Fall time	t_f		—	55	—	
	Turn−off time	t_{off}		—	170	—	
Total gate charge (Gate−source plus gate−drain)		Q_g	V_{DD} ≈ 48 V, V_{GS} = 10 V, I_D = 5 A	—	12	—	nC
Gate−source charge		Q_{gs}		—	8	—	
Gate−drain (“miller”) charge		Q_{gd}		—	4	—	

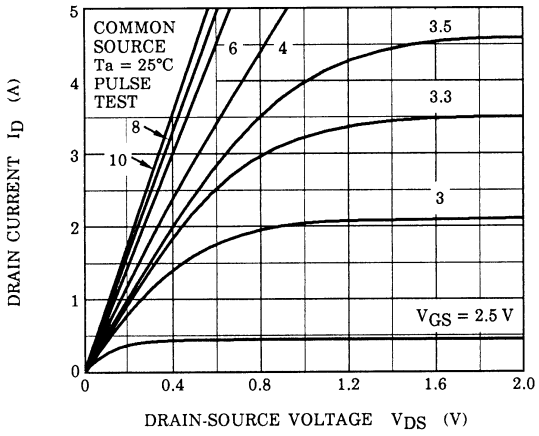
Source−Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	20	A
Forward voltage (diode)	V_{DSF}	I_{DR} = 5 A, V_{GS} = 0 V	—	—	−1.7	V
Reverse recovery time	t_{rr}	I_{DR} = 5 A, V_{GS} = 0 V, dI_{DR}/dt = 50 A/μs	—	70	—	ns
Reverse recovered charge	Q_{rr}		—	0.1	—	μC

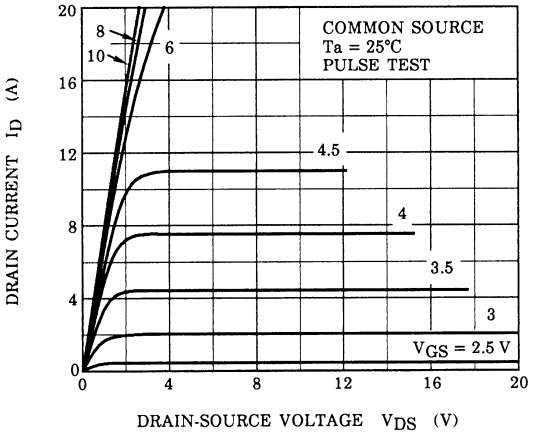
Marking



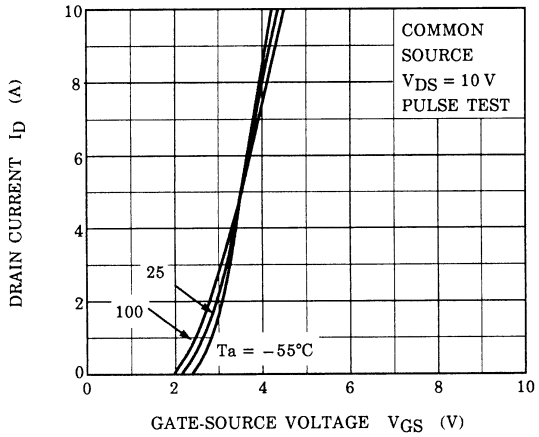
$I_D - V_{DS}$



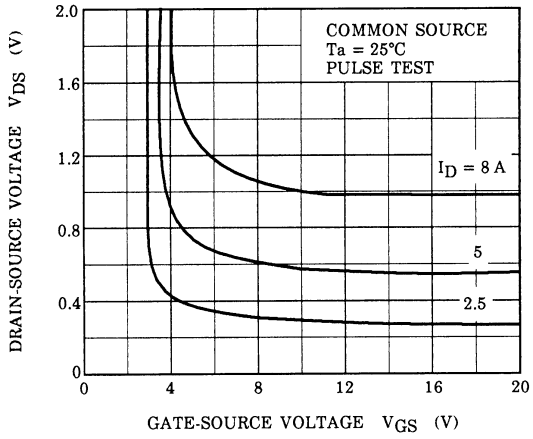
$I_D - V_{DS}$



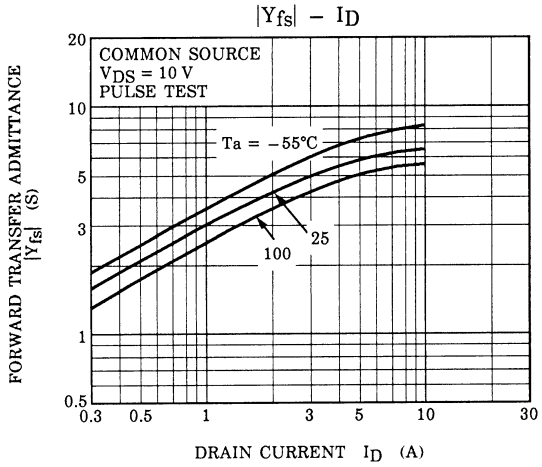
$I_D - V_{GS}$



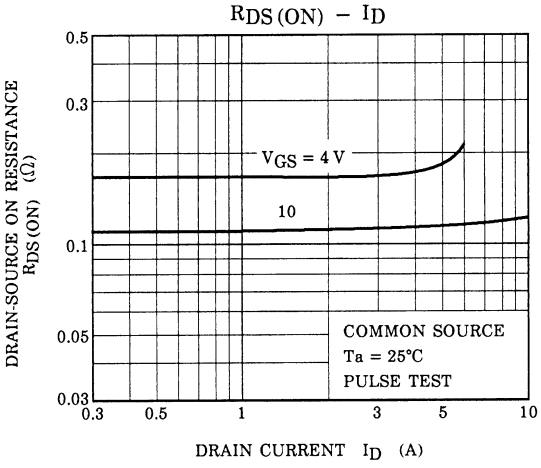
$V_{DS} - V_{GS}$



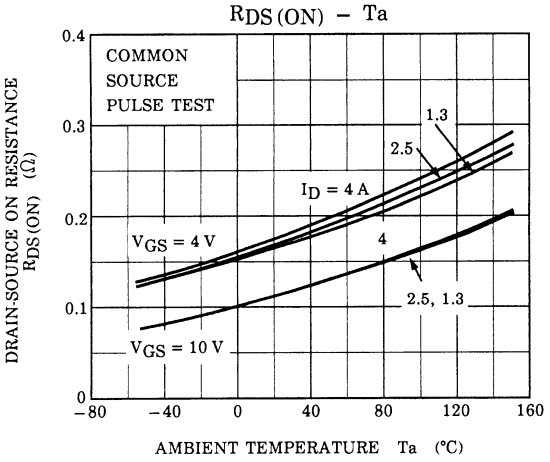
$|Y_{fs}| - I_D$



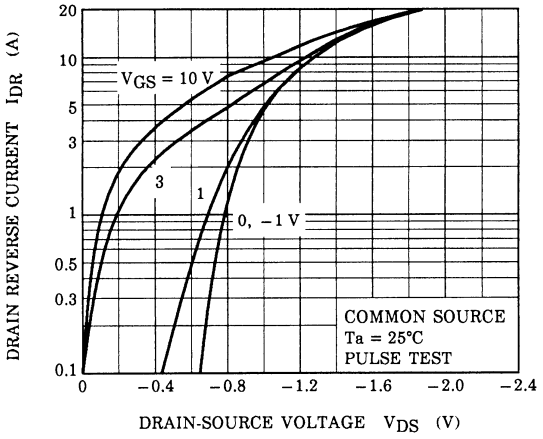
$R_{DS\,(ON)} - I_D$



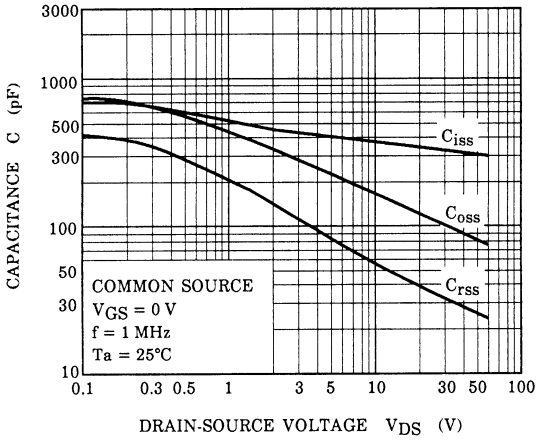
$R_{DS(ON)}$ – Ta



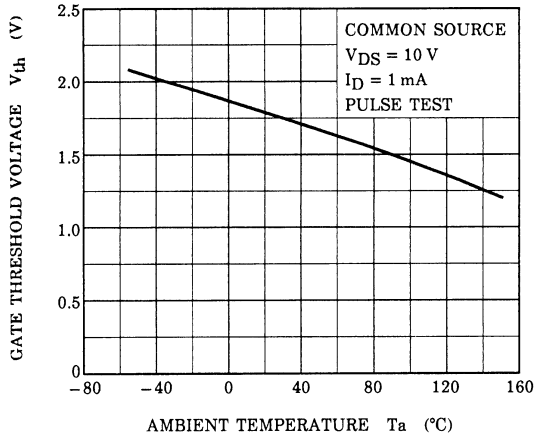
I_{DR} – V_{DS}



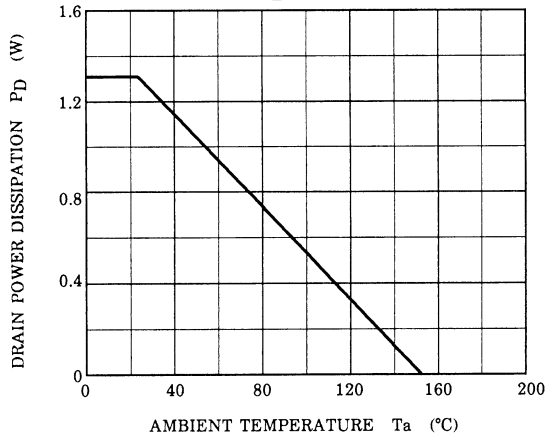
CAPACITANCE – V_{DS}



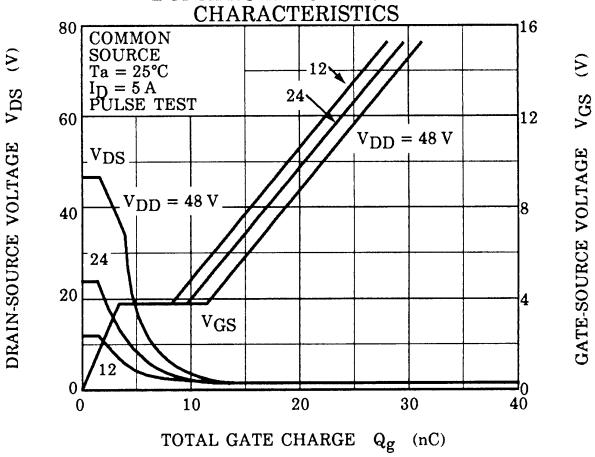
V_{th} – Ta



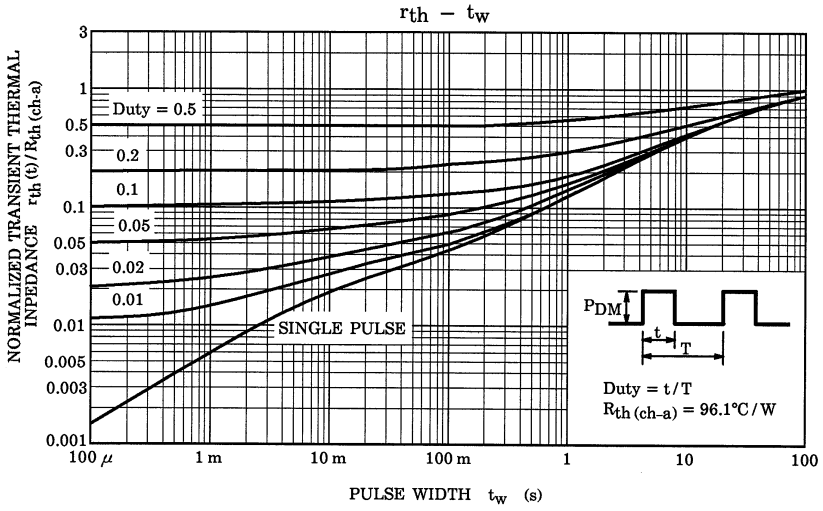
P_D – Ta



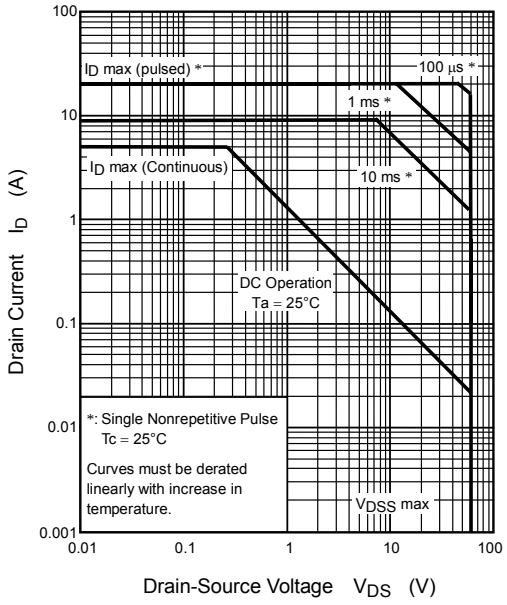
DYNAMIC INPUT / OUTPUT CHARACTERISTICS



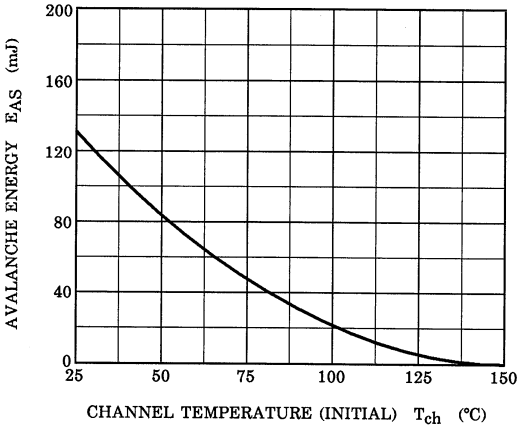
$r_{th} - t_w$

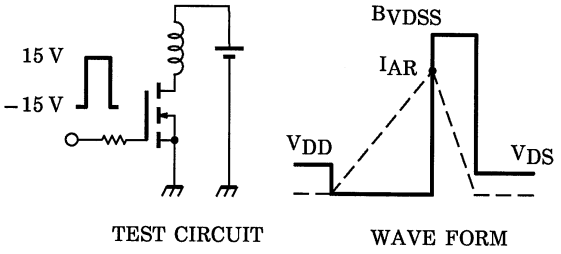


Safe Operating Area



$E_{AS} - T_{ch}$





TEST CIRCUIT WAVE FORM

$R_G = 25\ \Omega$
$V_{DD} = 25$ V, L = 7 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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